Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(high adj ("f.sub.max")) with MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:31
L2	2	(high adj ("f.sub.max")) same MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:31
L3	4	(high adj ("f.sub.max")) and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:33
L4	109	(("f.sub.max")) and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:44
L5	9	(("f.sub.max")) with MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:34
L6	18	(("f.sub.max")) same MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:35
L7	0	(("f.sub.max")) near MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:34
L8	73	(("f.sub.max")) and MOSFET and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 08:39

L10	26	(("f.sub.max")) and MOSFET and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 09:12
L12	772	(257/382).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 09:44
L13	867	(257/382,383,384,412,413.ccls. and silicide and metal) and @ad<="20010820"	USPAT	OR	ON	2005/10/07 10:10
L14	326	(257/383).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 10:10
L15	564	(257/384).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
L16	1177	(257/412).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
L17	496	(257/413).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
L18	7	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:24
L19	22	("438"/$.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:24
L20	32	("257"/$.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:24

L21	32	(semiconductor and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:25
L22	23	(semiconductor and MOSFET and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:25
L23	29	(semiconductor and MOSFET and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:29
L24	28	("257"/$.ccls. and MOSFET and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:28
L25	17	("438"/$.ccls. and MOSFET and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/07 13:26
S1	192	((mosfet and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820") and semiconductor	USPAT; JPO	OR	ON	2003/03/17 10:04
S9	213	mosfet and silicide and (first adj metal) and (second adj metal)	USPAT; EPO; JPO; DERWENT	OR	ON	2003/03/17 11:22
S11	64	mosfet and silicide and (first adj metal) and (second adj metal)	US-PGPUB	OR	ON	2003/03/17 11:00
S12	0	S11 and @ad<="20010820"	USPAT; EPO; JPO; DERWENT	OR	ON	2003/03/17 11:00
S13	608	(mosfet or dram or cmos) and silicide and (first adj metal) and (second adj metal)	USPAT	OR	ON	2005/04/22 12:04
S14	594	S13 and @ad<="20010820"	USPAT; EPO; JPO; DERWENT	OR	ON	2003/03/17 11:02
S15	594	S13 and @ad<="20010820"	USPAT; EPO; JPO; DERWENT	OR	ON	2003/03/17 11:02
S16	594	S13 and @ad<="20010820"	USPAT	OR	ON	2003/03/17 11:02

S17	176	(mosfet or dram or cmos) and silicide and (first adj metal) and (second adj metal)	US-PGPUB	OR	ON	2003/03/17 11:18
S18	12	mosfet and silicide and (first adj metal) and (second adj metal)	JPO; DERWENT	OR	ON	2003/03/17 11:22
S19	769	(257/382,383,384,412,413.ccls. and silicide and metal) and @ad<="20010820"	USPAT	OR	ON	2003/03/17 11:27
S20	83	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2005/04/22 12:05
S21	1306	(438/586,533,592,197.ccls. and silicide) and @ad<="20010820"	USPAT	OR	ON	2003/03/17 11:29
S27	533	(257/382).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 09:44
S28	236	(257/383).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 10:10
S29	410	(257/384).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
S30	833	(257/412).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
S31	345	(257/413).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/07 13:23
S32	10	(("5691212") or ("5268330") or ("6388294") or ("5753552") or ("6218276") or ("5783479") or ("5739573") or ("4868617") or ("6218276") or ("5736455") or ("6198143")).PN.	USPAT; USOCR	OR	OFF	2005/04/28 11:33
S33	2009	438/586,533,592,197.ccls.	USPAT	OR	ON	2003/03/14 14:53

S34	1178	257/382,383,384,412,413.ccls.	USPAT	OR	ON	2003/03/14 14:55
S35	1219	438/586,533,592,197.ccls. and silicide and metal	USPAT	OR	ON	2003/03/14 15:22
S36	783	257/382,383,384,412,413.ccls. and silicide and metal	USPAT	OR	ON	2003/03/17 10:05
S37	769	(257/382,383,384,412,413.ccls. and silicide and metal) and @ad<="20010820"	USPAT	OR	ON	2005/10/07 09:44
S38	1200	(438/586,533,592,197.ccls. and silicide and metal) and @ad<="20010820"	USPAT	OR	ON	2003/03/14 15:23
S39	53	257/382,383,384,412,413.ccls. and silicide and (first adj metal) and (second adj metal)	USPAT	OR	ON	2003/03/14 15:36
S40	88	438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)	USPAT	OR	ON	2003/03/14 15:25
S41	51	(257/382,383,384,412,413.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2003/03/17 10:05
S42	83	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2003/03/17 11:26
S43	201	mosfet and silicide and (first adj metal) and (second adj metal)	USPAT	OR	ON	2003/03/17 10:25
S44	198	(mosfet and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2005/04/22 11:20
S45	192	((mosfet and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820") and semiconductor	USPAT	OR	ON	2003/03/17 10:05
S52	1	("4868617").PN.	USPAT; USOCR	OR	OFF	2002/09/25 13:32
S54	269	(mosfet and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:25
S56	587	(gate with silicide) and ((first adj metal) and (second adj metal)) and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:26

S57	5	(gate with silicide) and ((first adj ("ILD")) and (second adj ("ILD"))) and ((first adj metal) and (second adj metal)) and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:30
S58	132	(gate with silicide) and ((first adj (("ILD") or insulating or dielectric)) and (second adj (("ILD") or insulating or dielectric)) and ((first adj metal) and (second adj metal)) and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:32
S59	116	(gate with silicide) and ((first adj (("ILD") or insulating or dielectric)) and (second adj (("ILD") or insulating or dielectric))) and ((first adj metal) and (second adj metal)) and @ad<="20010820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:33
S60	1	("5804852").PN.	USPAT; USOCR	OR	OFF	2005/04/22 13:13
S61	675	(mosfet or dram or cmos) and silicide and (first adj metal) and (second adj metal) and @ad<="20010820"	USPAT	OR	ON	2005/04/22 12:05
S62	117	((mosfet or dram or cmos) with silicide) and (first adj metal) and (second adj metal) and @ad<="20010820"	USPAT	OR	ON	2005/04/22 12:05
S63	93	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2005/04/25 12:55
S67	2	(("6177329") or ("6184121")).PN.	USPAT; USOCR	OR	OFF	2005/04/25 12:28
S68	1	("6376351").PN.	USPAT; USOCR	OR	OFF	2005/04/25 12:28
S69	861	(257/382,383,384,412,413.ccls. and silicide and metal) and @ad<="20010820"	USPAT	OR	ON	2005/04/28 10:37
S70	93	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820"	USPAT	OR	ON	2005/04/28 10:37
S71	7	(438/586,533,592,197.ccls. and silicide and (first adj metal) and (second adj metal)) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/10/07 13:23

S72	0	((438/586,533,592,197.ccls.) with MOSFET with silicide) and (first adj metal) and (second adj metal) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/04/28 10:39
S73	0	(("438"/$.ccls.) with MOSFET with silicide) and (first adj metal) and (second adj metal) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/04/28 10:39
S74	0	(("257"/$.ccls.) with MOSFET with silicide) and (first adj metal) and (second adj metal) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/04/28 10:39
S75	7	((semiconductor) with MOSFET with silicide) and (first adj metal) and (second adj metal) and @ad<="20010820" and (deep adj submicron)	USPAT	OR	ON	2005/04/28 10:39